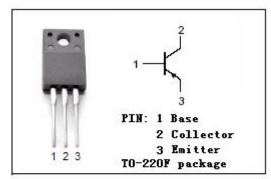




# isc Silicon PNP Power Transistor

#### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - :  $V_{(BR)CEO}$ = -30V(Min)
- · Low Collector Saturation Voltage-
  - :  $V_{CE(sat)} = -0.5V(Max)@ (I_C = -5A, I_B = -0.25A)$
- Complement to Type 2SD2219
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

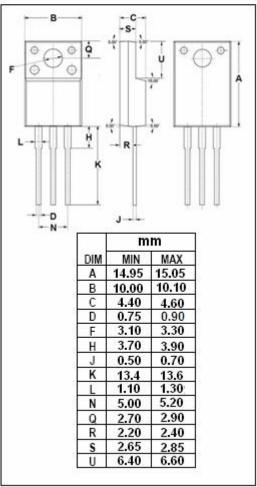


#### **APPLICATIONS**

• Designed for high-speed inverters, converters.



SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
Ic	Collector Current-Continuous	-12	Α
I <sub>CM</sub>	Collector Current-Pulse	-20	Α
P <sub>C</sub>	Collector Power Dissipation @T <sub>a</sub> =25℃	2	W
	Collector Power Dissipation @T <sub>C</sub> =25°C	25	] vv
TJ	Junction Temperature 150		$^{\circ}$ C
Tstg	Storage Temperature -55~1		$^{\circ}\! \mathbb{C}$





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2SB1468

#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

1j-25 C un	1j-25 C unless otherwise specified								
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -1mA; R <sub>BE</sub> = ∞	-30			V			
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -1mA; I <sub>E</sub> = 0	-60			V			
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -1mA; I <sub>C</sub> = 0	-6			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.25A			-0.5	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -40V; I <sub>E</sub> = 0			-100	μА			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4V; I <sub>C</sub> = 0			-100	μА			
h <sub>FE-1</sub>	DC Current Gain	Ic= -1A; V <sub>CE</sub> = -2V	70		280				
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -6A; V <sub>CE</sub> = -2V	30						
Switching Times									
t <sub>on</sub>	Turn-on Time			0.1		μς			
t <sub>stg</sub>	Storage Time	$V_{CC}^{-}$ -10V, $R_L^{-}$ 2 $\Omega$ , $I_{C}^{-}$ -5A; $I_{B1}^{-}$ - $I_{B2}^{-}$ -0.5A,		0.3		μS			
t <sub>f</sub>	Fall Time			0.03		μ \$			

### ♦ h<sub>FE-1</sub> Classifications

Q	R	S
70-140	100-200	140-280



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